



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

30 J Amst
M. Branson
12/6/02

In re Appln. Of: YOKOYAMA

DEC -4 2002

Serial No.: 08/992,767

TECHNOLOGY CENTER 2600

Filed: December 17, 1997

For: CONTACT STRUCTURE IN SEMICONDUCTOR....

Group: 2814

Examiner: DOUGLAS A. WILLE

DOCKET: NEC 19654 CON

BOX RCE

Assistant Commissioner of Patents

Washington, D.C. 20231

AMENDMENT G WITH RCE

Dear Sir:

This Amendment is being filed in response to the Final Action mailed August 26, 2002.

A Request for Continued Examination (RCE) accompanies this Amendment.

Please amend the Application as follows: | 12/03/2002 AmonDAF1 00000104 08992767
01 FC:1202 100.00 CH 8.00 OP

IN THE CLAIMS:

Please amend claims 11 and 20, to read as follows:

11. (Amended) A semiconductor device including both a large-diameter contact hole and a small-diameter contact hole formed to penetrate through an insulator film formed on a semiconductor substrate to reach said semiconductor substrate, each of said large-diameter contact hole and said small-diameter contact hole having a constant-diameter portion formed on a lower portion thereof, and a funnel-shaped portion formed on an upper portion thereof to open or spread upward, said small-diameter contact hole being completely filled with a plug of a refractory conductive material which contacts said semiconductor substrate, and said large-diameter contact hole being partly filled by said refractory conductive material which covers a

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02 FC:1201 168.00 OP
03 FC:1202 180.00 OP

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